

AMENDMENTS TO THE CLAIMS

Claim amendments and status:

1. (Previously Presented) A semiconductor laser having a laser beam-emitting facet, the semiconductor laser comprising:

a light-emitting region formed on the laser beam-emitting facet;
an indicator region spaced at a distance from the light-emitting region; and
a three dimensional marker indicating the location of the light-emitting region, wherein the three dimensional marker is located in the indicator region, and wherein the three-dimensional marker is at least one of a concavity and a convexity formed on the laser beam-emitting facet in the indicator region.

2. (Canceled)

3. (Previously Presented) The semiconductor laser as claimed in claim 1, further comprising a light-shielding film covering at least the light-emitting region, the light shielding film having a small opening in part of the portion of the light shielding film covering the light-emitting region.

4. (Canceled)

5. (Previously Presented) The semiconductor laser as claimed in claim 3, wherein the light-shielding film further covers the three-dimensional marker.

6. (Previously Presented) The semiconductor laser as claimed in claim 3, further comprising a dielectric film provided between the laser beam-emitting facet and the light-shielding film, wherein part of the dielectric film is exposed at the small opening.

7. (Canceled)

8. (Previously Presented) A method of producing a semiconductor laser having a laser beam-emitting facet including a light-emitting region, the method comprising:

forming an indicator region at a location on the laser beam-emitting facet that has a prescribed positional relationship with the light-emitting region, the indicator region having a three dimensional marker located thereon, and wherein the three-dimensional marker is at least one of a concavity and a convexity formed on the laser beam-emitting facet in the indicator region;

forming a light-shielding film covering at least the light-emitting region; and

forming the light-shielding film within a small opening at a location having a prescribed positional relationship with the three-dimensional marker.

9. (Canceled)

10. (Previously Presented) The method as claimed in claim 8, wherein the forming of the indicator region and the forming of the small opening both utilize focused ion beam processing.

11. (Previously Presented) The method as claimed in claim 8, further comprising: irradiating at least the light-emitting region of the laser beam-emitting facet with a focused ion beam before forming of the indicator region.

12. (Previously Presented) The method as claimed in claim 8, further comprising: irradiating at least the light emitting region of the laser beam-emitting facet with a focused ion beam before the forming of the indicator region.

13. (Canceled)

14. (Withdrawn) An evanescent optical head system comprising:
an evanescent optical head for reading/writing of data from/to a recording medium using evanescent light; and

a semiconductor laser coupled to the evanescent optical head for emitting the evanescent light, the laser having a laser beam-emitting facet including a light-emitting region, the laser comprising:

an indicator region formed on the laser beam-emitting facet;
a light shielding film covering at least the light-emitting region; and
a small opening for emitting the evanescent light formed in the light-shielding
film at a location that has a prescribed positional relationship with the indicator region.

15. (Withdrawn) The evanescent optical head as claimed in claim 14, further
comprising a three-dimensional marker located in the indicator region.

16. (Previously Presented) A semiconductor laser assembly including a
semiconductor laser having a laser beam-emitting facet comprising:
a light-emitting region formed on the laser beam-emitting facet;
an indicator region formed at a region different from the light-emitting region; and
a three dimensional marker indicating the location of the light emitting region, wherein
the three dimensional marker is located in the indicator region, and wherein the three-
dimensional marker is at least one of a concavity and a convexity formed on the laser beam-
emitting facet in the indicator region.

17. (Canceled)

18. (Previously Presented) The semiconductor laser assembly as claimed in claim 16,
further comprising a light-shielding film covering at least the light-emitting region, the light
shielding film being formed with a small opening at part of the portion of the light shielding film
covering the light-emitting region.

19. (Previously Presented) The semiconductor laser assembly as claimed in claim 18,
wherein the light-shielding film further covers the three-dimensional marker.

20. (Previously Presented) The semiconductor laser assembly as claimed in claim 18,
further comprising a dielectric film provided between the laser beam-emitting facet and the light-
shielding film, part of the dielectric film being exposed at the small opening.